



RCE/2800

REQUEST FOR CONTINUED EXAMINATION (RCE) TRANSMITTAL Subsection (b) of 35 U.S.C. § 132, effective on May 29, 2000, provides for continued examination of an utility or plant application filed on or after June 8, 1995. See The American Inventors Protection Act of 1999 (AIPA).	<i>Application Number</i>	09/467,992 ✓
	<i>Filing Date</i>	December 20, 1999 ✓
	<i>First Named Inventor</i>	Leonard Forbes et al.
	<i>Group Art Unit</i>	2815 #16/RCE
	<i>Examiner Name</i>	Eugene Lee
	<i>Attorney Docket Number</i>	303.389US2 8/21/02

This is a Request for Continued Examination (RCE) under 37 C.F.R. § 1.114 of the above-identified application entitled CIRCUITS WITH A TRENCH CAPACITOR HAVING MICRO-ROUGHENED SEMICONDUCTOR SURFACES.

Submission required under 37 C.F.R. § 1.114

1. ☐ Consider the amendment(s)/reply under 37 C.F.R. § 1.116 previously filed on ☐
2. ☐ Consider the arguments in the Appeal Brief or Reply Brief previously filed on ☐
3. ☒ An Amendment Under 37 CFR § 1.116 (11 pages) is enclosed.
4. ☐ A new power of attorney (☐ pages) is enclosed.
5. ☒ An Information Disclosure Statement is enclosed (1 page)
 - a. 1 Form(s) 1449
 - b. 9 Copies of IDS Citations
6. ☒ A check in the amount of \$740.00 is attached to pay the RCE filing fee required under C.F.R. § 1.17(e).
7. ☒ The Commissioner is hereby authorized to credit overpayments or charge any fees set forth in 37 C.F.R. §§ 1.16 through 1.18 to Deposit Account No. 19-0743.
8. ☐ A petition for extension of time in the prior application (☐ pages) is enclosed along with a check in the amount of \$☐ to pay the extension fee.
9. ☒ Other: Clean Version of Pending Claims (7 pages); Clean Version of Amended Specification Paragraph (1pg.); Red-line Drawing of Figure 1 (1pg); and Formal Drawings as amended (5 pgs.)

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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, Box RCE, Washington, D.C. 20231, on this 6th day of August, 2002.

Name

Amy Morarty

Signature

Amy Morarty

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EXPEDITED PROCEDURE - EXAMINING GROUP 2815

#18/F

Drawing
Changes
8/21/02
A. Smith

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Leonard Forbes et al.	Examiner:	Eugene Lee
Serial No.:	09/467,992	Group Art Unit:	2815
Filed:	December 20, 1999	Docket:	303.389US2
Title:	CIRCUITS WITH A TRENCH CAPACITOR HAVING MICRO-ROUGHENED SEMICONDUCTOR SURFACES		

AMENDMENT & RESPONSE UNDER 37 C.F.R. § 1.116

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In response to the final Office Action mailed May 6, 2002, please amend the application as follows:

IN THE DRAWINGS

The drawings were objected to under 37 C.F.R. 1.83(a) for failing to show every feature of the invention specified in the claims. The Examiner requested that the trench capacitor formed in a trench and coupled to the "first source/drain region" 106 be shown in FIG. 1 or the feature canceled from the claims.

FIG. 1 has been amended to include a reference number 110' that identifies the "first plate," which is described in the specification on page 6, lines 27-28 as being "integral with" second source/drain region 110.

The Examiner requested the corrected drawing based on his understanding that the *first source/drain region 106* is coupled to trench capacitor 119. In fact, it is the *second source/drain region 110* that is coupled to the trench capacitor by virtue of the first plate 110' being integral with the second source/drain region 110. The claims have also been amended to make this more clear, as described in greater detail below.

By adding reference number 110' identifying the first plate in FIG. 1, it is easier to see how the trench capacitor is coupled to the second source/drain region 110 of the transistor, i.e., because first plate 110' of the capacitor and the second source/drain region 110 of the transistor 119 constitute the same structure.